

AMENDMENTS TO THE CLAIMS

Claims 1-36 (Canceled)

Claim 37 (Previously Presented) A method of growing a single crystal comprising:
bringing a seed crystal into contact with a raw material melt which is heated and melted within a crucible by a resistance heating heater and growing a single crystal; and
rotating the crucible without rotating a blade member having a screw form in the crucible in the raw material melt during said growing, the blade member being located at a position corresponding to the center of rotation of the crucible and adjacent to the inside bottom of the crucible, so as to stir the raw material melt in the crucible;
wherein said growing a single crystal includes slowly cooling the raw material melt with which the seed crystal makes contact below a liquid level of the raw material melt to precipitate the single crystal on the surface of the seed crystal such that a difference in temperature of the raw material melt between different positions along an extent from the liquid level to a depth of 10cm is in a range of -0.5° to 0°C.

Claim 38 (Previously Presented) The method of claim 37, wherein the seed crystal is rotated during said rotating the crucible.

Claim 39 (Previously Presented) The method of claim 38, wherein said growing comprises growing a single crystal of an oxide.

Claim 40 (Previously Presented) The method of claim 39, said growing a single crystal of an oxide comprises growing a single crystal of a borate type oxide.

Claim 41 (Previously Presented) The method of claim 40, wherein the borate type oxide is $\text{CsLiB}_5\text{O}_{10}$ or an oxide obtained by partially substituting at least one of Cs and Li of $\text{CsLiB}_5\text{O}_{10}$ with at least one type among other alkali metal elements and alkali earth metal elements.

Claim 42 (Previously Presented) The method of claim 41, wherein the oxide is doped with at least one of Al and Ga elements.

Claim 43 (Previously Presented) The method of claim 40, wherein the borate type oxide is represented by $\text{Gd}_x\text{Y}_{1-x}\text{Ca}_4\text{O}(\text{BO}_3)_3$ ($0 < x < 1$) and said growing comprises a pulling method.

Claim 44 (Previously Presented) The method of claim 39, wherein the single crystal of an oxide is LiNbO_3 , LiTaO_3 , a high-temperature superconductive oxide material or a heat-electricity-conversion oxide material.

Claim 45 (Previously Presented) The method of claim 37, wherein said growing comprises growing a single crystal of an oxide.

Claim 46 (Previously Presented) The method of claim 45, said growing a single crystal of an oxide comprises growing a single crystal of a borate type oxide.

Claim 47 (Previously Presented) The method of claim 46, wherein the borate type oxide is $\text{CsLiB}_5\text{O}_{10}$ or an oxide obtained by partially substituting at least one of Cs and Li of $\text{CsLiB}_5\text{O}_{10}$ with at least one type among other alkali metal elements and alkali earth metal elements.

Claim 48 (Previously Presented) The method of claim 47, wherein the oxide is doped with at least one of Al and Ga elements.

Claim 49 (Previously Presented) The method of claim 46, wherein the borate type oxide is represented by $Gd_x Y_{1-x} Ca_4 O(BO_3)_3$ ($0 < x < 1$) and said growing comprises a pulling method.

Claim 50 (Previously Presented) The method of claim 45, wherein the single crystal of an oxide is $LiNbO_3$, $LiTaO_3$, a high-temperature superconductive oxide material or a heat-electricity-conversion oxide material.

Claim 51 (Currently Amended) The method of claim 37, wherein said slowly cooling comprises cooling the raw material melt with a temperature drop rate of $0.1^{\circ}C/day$.

Claims 52-55 (Cancel)